

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of manufacturing an integrated circuit substrate including a strained layer, the method comprising:
 - providing a base layer;
 - providing an insulating layer above the base layer;
 - providing a semiconductor layer above the insulating layer; and
 - forming a plurality of pillars in the base layer, the pillars extending in a direction closer to perpendicular than parallel to the base layer, wherein the pillars have a height greater than a width, and wherein the base semiconductor layer includes a top surface, the top surface being opposite the base layer and for including active components.
2. (Original) The method of claim 1, further comprising providing a compressive material in apertures associated with the pillars.
3. (Original) The method of claim 2, further comprising planarizing the compressive material until the base layer is reached.
4. (Original) The method of claim 1, wherein the semiconductor layer includes silicon.
5. (Original) The method of claim 1, wherein the insulative layer includes silicon dioxide.
6. (Original) The method of claim 1, wherein the base layer includes silicon.
7. (Original) The method of claim 1, wherein the pillars have a width of 2000-3000 Å.